

Efficient Red Perovskite Light-Emitting Diodes Based on Solution-Processed Multiple Quantum Wells

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This paper reports a facile and scalable process to achieve high performance red perovskite light-emitting diodes (LEDs) by introducing inorganic Cs into multiple quantum well (MQW) perovskites. The MQW structure facilitates the formation of cubic CsPbI₃ perovskites at low temperature, enabling the Cs-based QWs to provide pure and stable red electroluminescence. The versatile synthesis of MQW perovskites provides freedom to control the crystallinity and morphology of the emission layer. It is demonstrated that the inclusion of chloride can further improve the crystallization and consequently the optical properties of the Cs-based MQW perovskites, inducing a low turn-on voltage of 2.0 V, a maximum external quantum efficiency of 3.7%, a luminance of ≈ 440 cd m⁻² at 4.0 V. These results suggest that the Cs-based MQW LED is among the best performing red perovskite LEDs. Moreover, the LED device demonstrates a record lifetime of over 5 h under a constant current density of 10 mA cm⁻². This work suggests that the MQW perovskites is a promising platform for achieving high performance visible-range electroluminescence emission through high-throughput processing methods, which is attractive for low-cost lighting and display applications.

Organometal halide perovskite light-emitting diodes (PeLEDs) have received considerable attention due to their potential for solution-processed, low-cost displays, and lighting sources.^[1–4] In order to achieve high efficiency PeLEDs, it is a challenge to fabricate highly emissive thin perovskite layers with uniform

film morphology. The efficiency of 3D perovskites based LEDs is mainly limited by the nonradiative loss channels caused by defects or pin-holes in the emission layer.^[2] 2D organometal perovskites are naturally formed quantum wells with excellent film morphology, but previous study showed that their photoluminescence (PL) efficiency is very low at room temperature due to strong exciton–phonon interaction.^[5–7] Recent results showed that the photoluminescence quantum efficiency (PLQE) of the 2D perovskites can be significantly enhanced when multiple quantum well (MQW) structure forms with energy cascade.^[8] The high PLQE of the MQW perovskites is due to the fast energy transfer from the large bandgap QWs to small bandgap QWs where efficient radiative decay occurs.^[8,9] Consequently, the MQW-based PeLED can have high external quantum efficiency (EQE) up to 11.7% in near-infrared (NIR).^[8] An

interesting question is whether the MQW LEDs can achieve similar high performance in the visible range.

For visible emission PeLEDs, efficient green emission has been demonstrated by using 3D CH₃NH₃PbBr₃ films, while the EQE of red 3D perovskite LEDs is only 0.2%.^[1] The low efficiency of the red PeLEDs is mainly due to low PLQEs of the perovskite emission layers caused by the halide phase segregation of the I–Br mixed perovskite films used.^[10–12] Alternatively, CsPbI₃ perovskite nanocrystals with high PLQE and pure color emission seem to be a good candidate for red light emitters.^[13] By using atomic layer deposition (ALD) and cross-linking method, CsPbI₃ nanocrystal-based red LEDs showed a 5.7% EQE and a maximum luminance of 206 cd m⁻².^[14] The study demonstrates the promise of exploiting quantum confinement effects in achieving high performance red PeLEDs, although the device fabrication process still involves steps (e.g., ALD) that are time consuming and difficult to scale up.

In this work, we demonstrate a facile and scalable process to achieve high performance red PeLEDs by introducing inorganic cesium (Cs⁺) into MQW perovskites. The MQW structure facilitates the formation of cubic CsPbI₃ perovskites at low temperature, and the Cs-based QWs provide pure and stable red electroluminescence (EL). With the MQW perovskites there is no need to use ALD coated passivation layer, and the electron- and hole- transport layers can all be deposited through rapid

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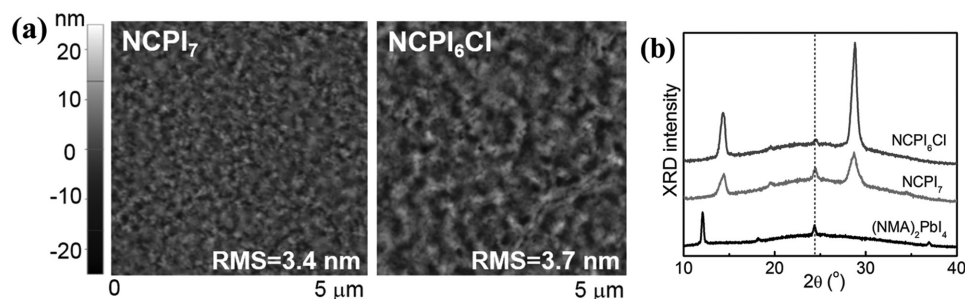


Figure 1. Perovskite MQW films. a) AFM height image of the NCPI₇ and NCPI₆Cl MQW films. b) XRD data of the (NMA)₂PbI₄, NCPI₇, and NCPI₆Cl films.

solution casting processes. Furthermore, the versatile synthesis of MQW perovskites provides freedom to control the crystallinity and morphology of the emission layer. For instance, we demonstrate that the inclusion of chloride can further improve the crystallization and consequently the optical properties of the Cs-based MQW perovskites, inducing a maximum EQE of 3.7%, a luminance of ≈ 440 cd m⁻² at a low voltage of 4.0 V, and a record lifetime of over 5 h under a constant current density of 10 mA cm⁻².

The red emission MQW perovskite films are prepared similar to our previously reported method.^[8] A precursor solution of 1-naphthylmethylamine iodide, cesium iodide (CsI), and PbI₂ with a molar ratio of 2:1:2 dissolved in a mixed solution of *N,N*-dimethylformamide (DMF) and dimethyl sulfoxide (volume ratio, 9:1) was used to deposit red emission MQW perovskite films, which are abbreviated as NCPI₇ films below. After spin-coating, the film is annealed at 110 °C for ≈ 5 min in a nitrogen glove box. Atomic force microscopy (AFM) measurement shows the NCPI₇ film is very uniform, with 3.4 nm root-mean-square roughness (Figure 1a).

We first study the structure properties of the NCPI₇ film by using X-ray diffraction (XRD) technique (Figure 1b). The NCPI₇ film exhibits strong peaks at $\approx 14.4^\circ$ and 28.8° , which is in accordance with the typical CsPbI₃ perovskite α -phase,^[15,16] indicating the formation of large-*n* QWs close to crystalline CsPbI₃ in our low-temperature-processed NCPI₇ film. We also note a weak XRD peak at 24° with the NCPI₇ film, consistent with the existence of the *n* = 1 QW ((NMA)₂PbI₄ (also shown in Figure 1b)). Therefore, the XRD result suggests that the NCPI₇ film is a mixture of *n* = 1 QW with large-*n* QW perovskite domains.

To further reveal the structure of the NCPI₇ film, optical characterization is fulfilled. Figure 2a shows absorbance and PL spectra of NCPI₇ MQW film. The absorption spectrum of the NCPI₇ film shows a strong exciton absorption peak at 2.44 eV and shoulders at 2.24 and 1.86 eV, which suggests that the NCPI₇ film is a mixture of perovskite QWs with different bandgaps. The different absorption intensities indicate that (NMA)₂PbI₄ (*n* = 1 QW) is the majority component of the NCPI₇ film, and there are also small fractions of *n* = 2 QW ((NMA)₂(CsPbI₃)PbI₄) and larger-*n* QWs in the NCPI₇ film.^[8] Accordingly, the PL spectrum shows several emission peaks at 2.42, 2.22, and 1.81 eV, which correspond well with the absorption peaks. The strongest absorption peak (2.44 eV) presents very weak PL emission which can only be distinguishable in logarithmic

scale. And the dominating PL emission peak (1.81 eV) is from the large-*n* QW, which is slightly blue-shifted to the PL emission peak of 3D CsPbI₃ perovskite (≈ 1.78 eV) (Figure S1, Supporting Information). The absorption and PL results indicate that energy transfer process occurs from large bandgap QWs to small bandgap QWs. PL excitation (PLE) measurements on the NCPI₇ film show that different emissions share same excitation peaks at 2.44 and 2.25 eV (Figure 2b), confirming that the process of energy transfer from *n* = 1 and *n* = 2 QWs contributes to the lower energy emissions. Figure 2c shows that the PL at different emission peaks have markedly different lifetimes. The PL lifetime increases as the emission photon energy decreases. The time-resolved PL measurements are consistent with a fast cascade energy transfer from the majority of *n* = 1 QWs to large-*n* QWs which may have much higher PL efficiencies. Figure 2d shows that the NCPI₇ film has relatively high PLQEs, $\approx 15\%$, even at very low excitation intensities. Those optical characterization results suggest that the NCPI₇ films have similar MQW structures as NIR emission NFPI₇ MQWs,^[8] which can give efficient radiative decay by cascade energy transfer and exciton confinement in the large-*n* QWs. We note that although CsPbI₃ cubic perovskite geometry is known to be formed at high temperature (>300 °C),^[17] our low temperature processing results suggest that the MQW structure can facilitate the formation of large-*n* QWs close to the CsPbI₃.^[18] This can be due to entropic stabilization of mixed cations, which has been observed in the mixtures of formamidinium (FA)-methylammonium or FA-Cs cations of perovskite solar cells.^[18,19]

The device architecture of red MQW LED based on the NCPI₇ film is indium tin oxide/polyethylenimine ethoxylated modified zinc oxide (ZnO, ≈ 20 nm)/perovskite MQWs (≈ 60 nm)/poly(9,9-dioctyl-fluorene-*co*-*N*-(4-butylphenyl)diphenylamine) (TFB, ≈ 60 nm)/molybdenum oxide (MoO_x, ≈ 7 nm)/gold (Au, ≈ 60 nm). The energy-level diagram is shown in Figure 3a, wherein the energy level values for NCPI₇ film were estimated by ultraviolet photoelectron spectroscopy (UPS) (Figure S2, Supporting Information) and optical measurements. The fabrication details can be found in the Experimental Section.

The device EL spectrum, current density–voltage–luminance (*J*–*V*–*L*) and EQE characteristics are also shown in Figure 3. The EL emission peak is at 689 nm (Figure 3b), which is ≈ 12 nm blue-shifted to the EL emission of 3D CsPbI₃ LED (Figure S3, Supporting Information). The LED device exhibits very pure red emission with Commission Internationale de l’Eclairage (CIE) color coordinates of (0.73, 0.27) (Figure 3c), which is almost the

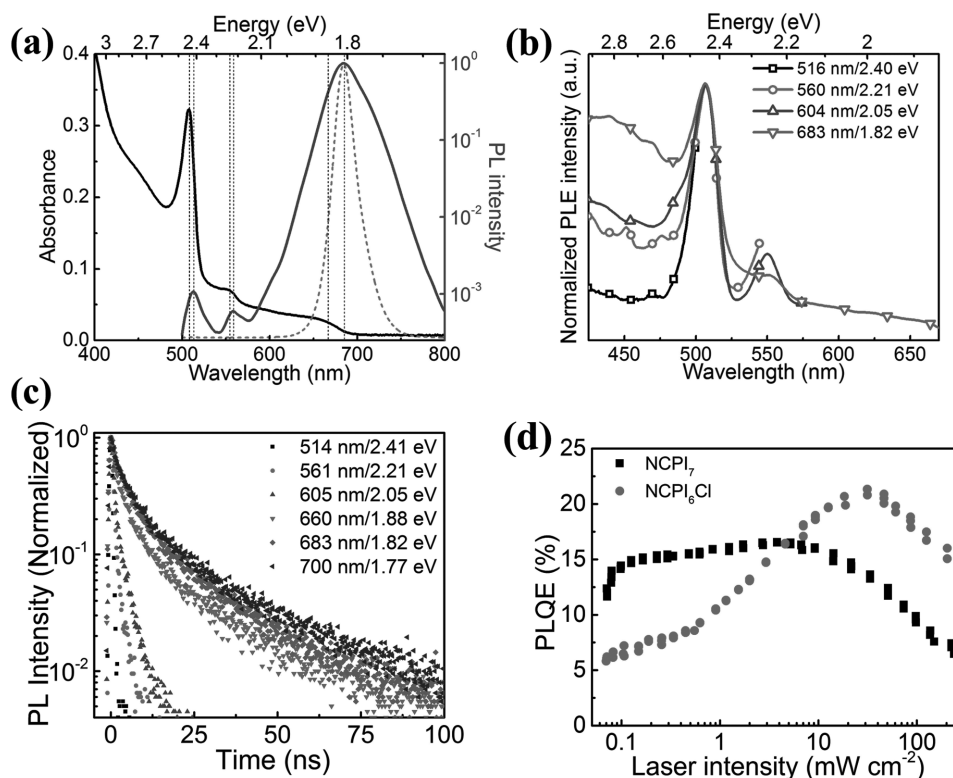


Figure 2. Optical properties of NCPI₇ and NCPI₆Cl films. a) Absorption and PL (445 nm excitation) spectra of the NCPI₇ MQW film deposited onto quartz substrates. The PL spectrum is normalized in log scale (blue curve) and linear scale (red dashed curve). b) PL excitation spectra of the NCPI₇ MQW film at various emission energies. c) Time-resolved PL decay transients of the NCPI₇ MQW film at different emission energies. Emission photons with smaller energy show longer PL decay time. d) Excitation-intensity-dependent PLQE of the NCPI₇ and NCPI₆Cl MQW film.

right corner of the CIE coordinates. The shapes of EL spectra do not change at different bias voltages (Figure S4, Supporting Information), unlike mixed I–Br 3D perovskite LEDs which show red-shifted EL emission upon device operation.^[14] The NCPI₇-MQW LED turns on at a voltage of 2.4 V (Figure 3d) and a luminance of 55 cd m⁻² can be achieved at a voltage of 4 V. The EQE of the LED reaches 2.4% at 3.1 V with a luminance of 15 cd m⁻² (Figure 3e). The average peak EQE of 43 devices is 1.5% with a relative standard deviation of 21%, showing good reproducibility of the device performance (Figure 3f).

Inclusion of chlorides in perovskite precursors have been shown to enhance the solar cell performance by improving the film optoelectronic properties.^[20–22] Here we explore the similar strategy to further improve the performance of our MQW perovskite LEDs. By replacing the CsI with CsCl in the precursor solution, we can obtain MQW films (abbreviated as NCPI₆Cl below) with better optical properties than NCPI₇ MQW film. The absorption, PL and PLE spectra of the NCPI₆Cl film exhibit consistent results as NCPI₇ film (Figure S5, Supporting Information), suggesting the NCPI₆Cl film consists of similar self-organized MQWs as those in the NCPI₇ film.

It has been widely observed that Cl incorporation can improve the crystallinity in 3D perovskites.^[23] We find that the similar improvement occurs in the formation of MQW perovskites. X-ray photoelectron spectroscopy (XPS) data show the presence of trace amount of chloride ions in the MQW perovskites (Figure S6, Supporting Information).

The Cs atomic ratio in NCPI₆Cl film is 11.1%, while that in NCPI₇ film is 7.5%, indicating the incorporation of Cl favors the growth of larger-*n* QWs in the MQW perovskites. This hypothesis is supported by the XRD measurement, where NCPI₆Cl shows much narrower XRD peaks (Figure 1b). The full-width half maximum value of XRD peak at 14.4° of NCPI₆Cl and NCPI₇ are 0.58° and 0.75°, respectively. The average crystal sizes of NCPI₆Cl and NCPI₇ are 15 and 10 nm, respectively, which is also consistent with the AFM measurement (Figure 1a). All these results suggest that the inclusion of chlorides can change the crystal formation kinetics in the Cs-based MQW perovskites.^[24] We believe the improvement mechanism of MQW perovskite crystallinity by incorporating chlorine is similar to the case of 3D perovskites,^[25–27] i.e., chlorine atoms participate in the formation of an intermediate phase, followed by exchanged by iodine atoms and repelled out of the perovskite network. The existence of the intermediate phase promotes the formation of compact films with relatively large crystalline domains. We note however that in the case of 3D MAPbI₃ perovskite, chlorine can easily escape from the perovskite film through sublimation of MAcl or volatilization of HCl and MA gas. In the case of the MQW structure, the organic cations are bulky; therefore, the sublimation and volatilization processes are suppressed. This results in a higher content of chlorine residue in the MQW film. It is also worth mentioning that it has been theoretically and experimentally validated that chlorine residue

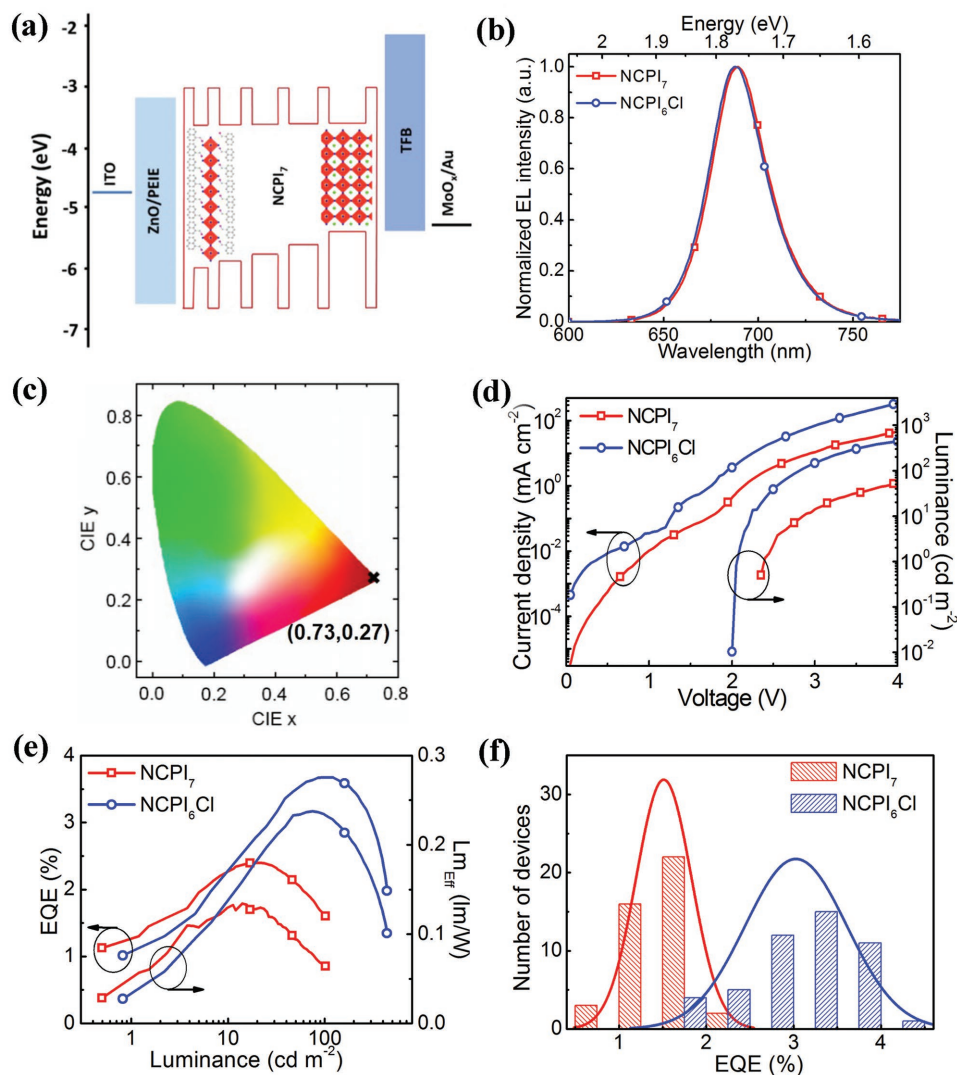


Figure 3. Device characteristics of the NCPI₇ and NCPI₆Cl MQW perovskite LEDs. a) Flat-band energy level diagram (NCPI₇). The energy level values besides NCPI₇ were taken from the literature.^[2] b) EL spectra of the NCPI₇ and NCPI₆Cl devices. c) Corresponding CIE coordinate of NCPI₇ device. d) Dependence of current density and luminance on the driving voltage. e) EQE and luminous efficacy versus luminance. f) Histograms of peak EQEs measured from NCPI₇ and NCPI₆Cl devices.

can positively impact the electronic properties of perovskite films by passivating the defects and reduce charge recombination.^[28–30] Transient PL measurement shows that the carrier lifetime is increased in NCPI₆Cl (Figure 2; Figure S5, Supporting Information), indicating Cl helps to reduce the defects in the MQW structures.^[31] As a result, the maximum PLQEs of NCPI₆Cl film is enhanced, reaching up to ≈20% (Figure 2d).

The EL emission peak of LEDs based on the NCPI₆Cl film is 688 nm (Figure 3b), which is almost same as that of the NCPI₇ devices. The champion NCPI₆Cl LED turns on at a low voltage of 2.0 V, which is 0.4 V lower than the NCPI₇ device. The lower turn-on voltage can be due to the better charge transport in the NCPI₆Cl film with improved crystallinity. A high luminance of ≈440 cd m⁻² is achieved at 4.0 V. The EQE reaches to 3.7% at 2.8 V with a luminance of ≈100 cd m⁻², which is increased by over 50% compared with the NCPI₇ devices. The EQE enhancement

of the NCPI₆Cl device is consistent with the improved PLQE of the NCPI₆Cl film (Figure 2d). The EQE histogram for 48 devices shows an average peak EQE of 3.0% with a relative standard deviation of 19%. Moreover, the peak luminous efficacy of NCPI₆Cl LED is 0.24 lm W⁻¹ at a brightness of ≈75 cd m⁻². These results suggest that our Cs-based MQW LED is among the best performing red perovskite LEDs (Table S1, Supporting Information). We note that the NCPI₆Cl MQW LEDs have excellent operation stability. The EQE of NCPI₆Cl devices dropped to half of the initial value after ≈5 h under a constant driving current density of 10 mA cm⁻² (Figure 4a). The lifetime is doubled compared to previous reported NIR emission MQW perovskite LEDs under the same driving condition,^[8] and is a new record for PeLEDs. The shape of the EL spectra remains unchanged upon long-term bias (Figure 4b). We believe that the improved device reliability can be attributed to the intrinsic stability of Cs-based perovskite films.^[15,18]

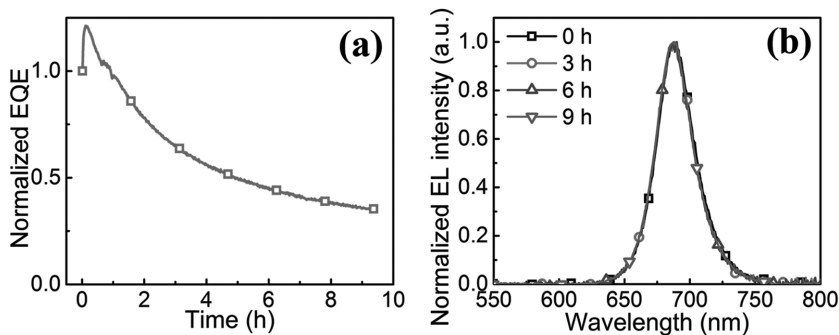


Figure 4. Stability measurements on NCPI₆Cl MQW perovskite LEDs. a) Normalized EQE for an NCPI₆Cl EL device tested at a constant current density of 10 mA cm⁻². b) EL spectra of the NCPI₆Cl device upon long-term bias.

We show that by using cesium-based self-organized perovskite MQWs, efficient and high-brightness red LEDs with good stability can be achieved. The inclusion of chloride can promote the formation of perovskite MQWs with high crystallization and further improved optical properties. Our results demonstrate that the MQW perovskites is a promising platform that allows achieving high performance visible-range EL emissions through high-throughput manufacturing processes, which is attractive for low-cost lighting and display applications.

Experimental Section

Synthesis and Materials Preparation: Colloidal ZnO nanocrystals were synthesized by a solution-precipitation process^[32] with some modifications. NCPI₇ and NCPI₆Cl precursor solutions were prepared similar to the previously reported method.^[8] CsPbI₃ precursor solutions were prepared by dissolving CsI and PbI₂ with molar ratio of 1:1 in DMF (10 wt%).

Device Fabrication: A detailed description of device fabrication can be found elsewhere.^[8] Here, the TFB layers were deposited from an *m*-xylene solution (13 mg mL⁻¹) at 2000 rpm.

Device Characterization: A detailed description of all perovskite LED device characterizations can be found elsewhere.^[8] The devices were swept from zero bias to forward bias at 0.05 V s⁻¹. The time evolution of EQEs was measured using the same testing system at room temperature in a nitrogen-filled glove box.

Film Characterization: AFM images were taken using a Park XE7 atomic force microscope in noncontact mode. UV-vis absorbance and PL spectra of the perovskite films were measured using an Agilent Cary 5000 UV-vis spectrophotometer with an integrating sphere and a HITACHI F-4600 fluorescent spectrophotometer, respectively. The excitation spectra and time resolved fluorescence spectra of the perovskite films were obtained by using an Edinburgh Instruments (FLS920) spectrometer. Here, the time-resolved PL excitation fluence is ≈4 nJ cm⁻² from an EPL-405 pulsed diode laser. A three-step technique combining laser, optical fiber, spectrometer, and integrating sphere was used to obtain PLQE of perovskite films.^[33] UPS and XPS spectra were collected on a Thermo ESCALAB-250Xi spectrometer (He I UV radiation source, 21.2 eV) and a Thermo ESCALAB 250 equipment, respectively.

Supporting Information

Supporting Information is available from the Wiley Online Library or from the author.

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Keywords

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